

V

$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	-131	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	-83	
I_{DM}	Pulsed Drain Current	-524	
$P_D @ T_C = 25^\circ\text{C}$	Power Dissipation	69	W
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-to-Source Voltage	± 20	V
$T_J \quad T_{STG}$	Operating Junction and Storage Temperature Range	-55 to +150	$^\circ\text{C}$

R_{JC}	Junction-to-case	—	1.8	/W
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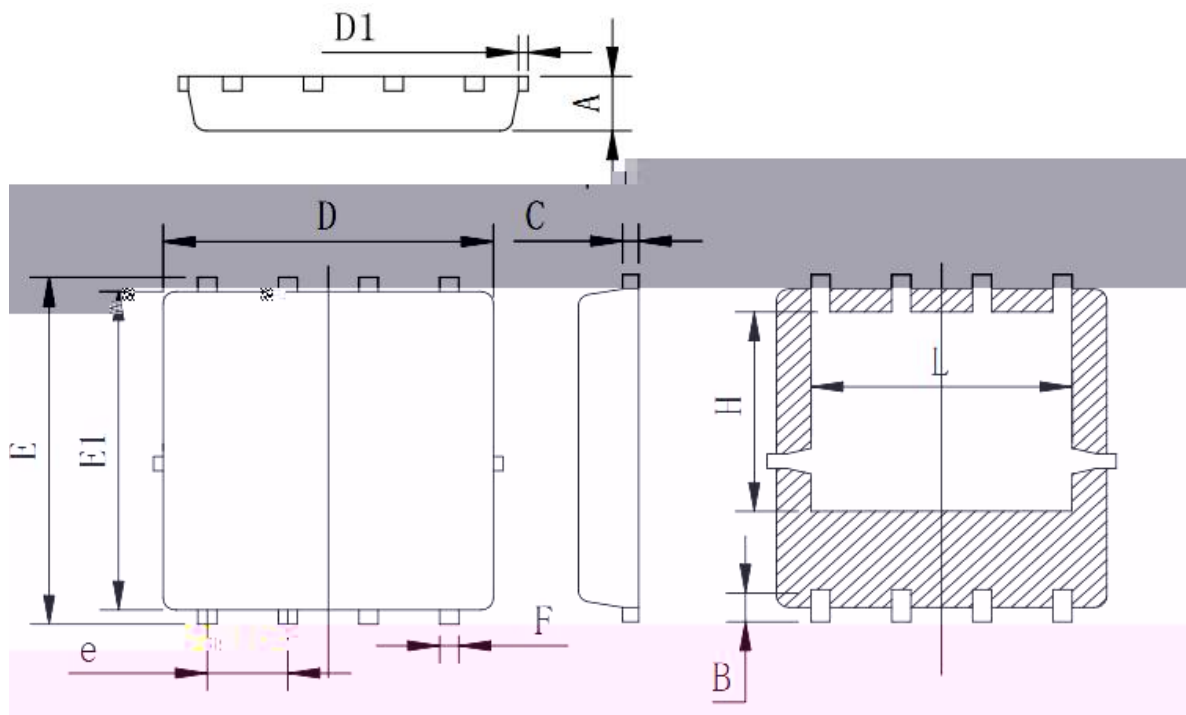
@ $T_A=25$ unless otherwise specified

$V_{(BR)DSS}$	Drain-to-Source breakdown voltage	-30	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$R_{DS(on)}$	Static Drain-to-Source on-resistance	—	1.9	2.5	m	$V_{GS} = -10V, I_D = -20A$
		—	2.7	3.6		$V_{GS} = -4.5V, I_D = -20A$
$V_{GS(th)}$	Gate threshold voltage	-1	—	-2.5	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
I_{DSS}	Drain-to-Source leakage current	—	—	-1	μA	$V_{DS} = -30V, V_{GS} = 0V$
I_{GSS}	Gate-to-Source forward leakage	—	—	100	nA	$V_{GS} = 20V$
		—	—	-100		$V_{GS} = -20V$
C_{iss}	Input capacitance	—	12750	—	pF	$V_{GS} = 0V$
C_{oss}	Output capacitance	—	1330	—		$V_{DS} = -15V$
C_{rss}	Reverse transfer capacitance	—	1200	—		$f = 1MHz$
Q_g	Total gate charge	—	20	—	nC	$I_D = -20A,$
Q_{gs}	Gate-to-Source charge	—	2.5	—		$V_{DS} = -15V,$
Q_{gd}	Gate-to-Drain("Miller") charge	—	3	—		$V_{GS} = -10V$
$t_{d(on)}$	Turn-on delay time	—	20	—	ns	$V_{GS} = -10V, V_{DS} = -15V,$ $R_{GEN} = 3, R_L = 0.75$
t_r	Rise time	—	4	—		
$t_{d(off)}$	Turn-Off delay time	—	23	—		
t_f	Fall time	—	37	—		

I_S	Continuous Source Current (Body Diode)	—	—	-131	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode)	—	—	-524	A	
V_{SD}						

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Calculated continuous current based on maximum allowa K I



Symbol	Min	Typ	Max
A	0.90	0.95	1.00
B	0.48	0.58	0.68
C	0.20	0.254	0.30
D	5.00	5.20	5.40
D1			0.15
E	5.00	6.05	6.20



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